SOFT ORANGE Item No.: 180622

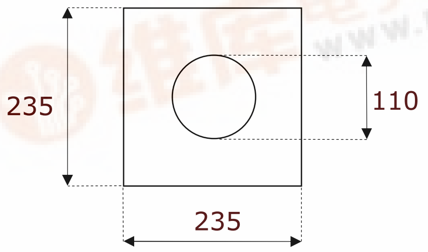
1. This specification applies to GaAsP / GaP LED Chips

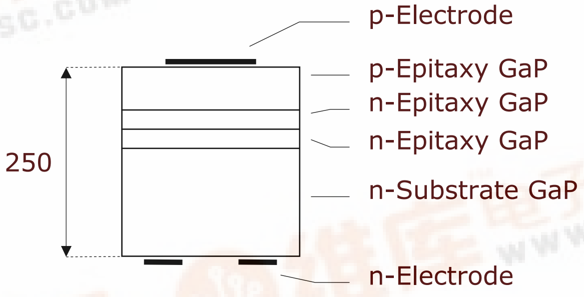
2. Structure

2.1 Mesa structure

2.2 Electrodes
p-side (anode) Au alloy
n-side (cathode) Au alloy

3. Outlines (dimensions in microns)





Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	*Symbol*	*Conditions*	*min*	*typ*	*max*	*Unit*
Forward voltage	V_F	I_F = 2 mA		1,85	2,00	V
Reverse current	I_R	V_R = 5 V			10	µA
Luminous intensity *	I_V	I_F = 2 mA	180	250		µcd
Peak wavelength	λ_P	I_F = 2 mA		610		nm

* On request, wafers will be delivered according to luminous intensity classes
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top
2) back contact on top

6. Labeling

Type	Lot No.	I_V typ min max	Quantity